R07DS0990EJ0100

Rev.1.00

Dec 27, 2012

μ**ΡΑ2630**Τ1R

P-CHANNEL MOSFET -12 V, -7.0 A, $28 \text{ m}\Omega$

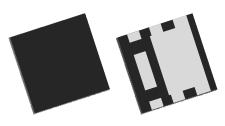
Description

The μ PA2630T1R is P-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- -1.8V drive available
- Low on-state resistance
 - ---- $R_{DS (on)1} = 28 \text{ m}\Omega \text{ MAX}. (V_{GS} = -4.5 \text{ V}, I_D = -3.5 \text{ A})$
 - ---- $R_{DS (on)2} = 35 \text{ m}\Omega \text{ MAX}. (V_{GS} = -2.5 \text{ V}, I_D = -3.5 \text{ A})$
 - ---- $R_{DS (on)2} = 59 \text{ m}\Omega \text{ MAX}. (V_{GS} = -1.8 \text{ V}, I_D = -3.5 \text{ A})$
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020

Ordering Information

Part Number	Package	
μPA2630T1R-E2-AX* ¹	6pinHUSON2020	

Note: *1.Pb-free (This product does not contain Pb in the external electrode and other parts.)

Absolute Maximum Ratings (T_A = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 V$)	V _{DSS}	-12	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	∓8	V
Drain Current (DC)	I _{D(DC)}	∓7.0	Α
Drain Current (pulse) *1	I _{D(pulse)}	∓28	Α
Total Power Dissipation (5 s) *2	Ρ _T	2.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Notes: ∗1. PW≤10 µs, Duty Cycle≤1%

*2. Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt



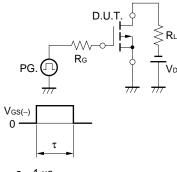
Electrical Characteristics (T_A = 25°C)

Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μA	V_{DS} = -12 V, V_{GS} = 0 V
Gate Leakage Current	I _{GSS}			∓10	μA	V _{GS} = ∓8 V, V _{DS} = 0 V
Gate Cut-off Voltage	V _{GS(off)}	-0.4		-1.1	V	V_{DS} = -10 V, I_{D} = -1 mA
Forward Transfer Admittance *1	y _{fs}	8.5			S	V_{DS} = -5 V, I _D = -3.5 A
Drain to Source On-state	R _{DS(on)1}		20.5	28	mΩ	V_{GS} = -4.5 V, I_{D} = -3.5 A
Resistance *1	R _{DS(on)2}		25.7	35	mΩ	V_{GS} = -2.5 V, I _D = -3.5 A
	R _{DS(on)3}		34.9	59	mΩ	V_{GS} = -1.8 V, I _D = -3.5 A
Input Capacitance	C _{iss}		1260		pF	V_{DS} = -10 V, V_{GS} = 0 V,
Output Capacitance	C _{oss}		240		pF	f = 1.0 MHz
Reverse Transfer Capacitance	C _{rss}		188		pF	
Turn-on Delay Time	t _{d (on)}		9.2		ns	$I_D = -3.5 \text{ A}, V_{DD} = -6.0 \text{ V},$
Rise Time	tr		3.9		ns	V_{GS} = -4.0 V, R_{G} = 6 Ω
Turn-off Delay Time	t _{d (off)}		76		ns	
Fall Time	t _f		49		ns	
Total Gate Charge	Q _G		11.3		nC	$I_D = -7.0 \text{ A}$, $V_{DD} = -9.6 \text{ V}$,
Gate to Source Charge	Q _{GS}		1.7		nC	V _{GS} = -4.5 V
Gate to Drain Charge	Q _{GD}		2.8		nC	
Body Diode Forward Voltage *1	V _{F(S-D)}			1.5	V	I _F = 7.0 A, V _{GS} = 0 V

Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME

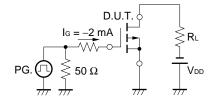
Vdd



 $\tau = 1 \, \mu s$, Duty Cycle ≤ 1%

Vgs(-) VGS Wave Form 0 10% 90% Vgs Vds(-) 90% 90% Vds V_{DS} Wave Form 10% 10% 0 tf tr td(on) td(off) tor toff

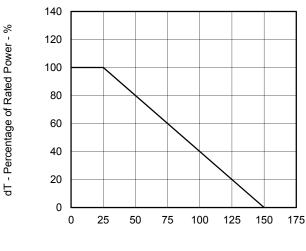
TEST CIRCUIT 2 GATE CHARGE





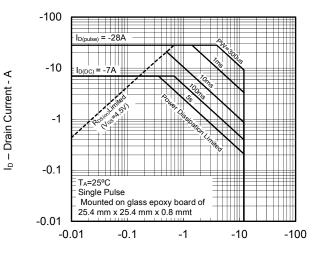
Typical Characteristics ($T_A = 25^{\circ}C$)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

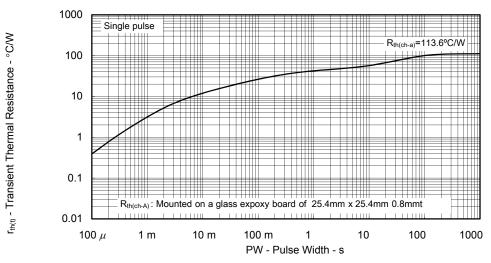


T_A -Ambient Temperature - °C



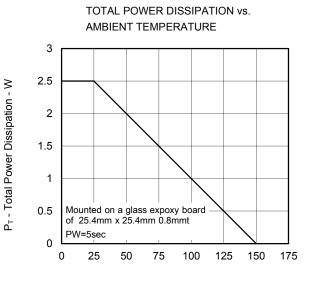


V_{DS} - Drain to Source Voltage - V

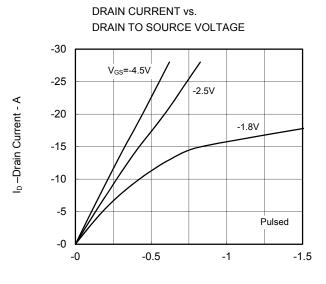


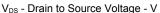


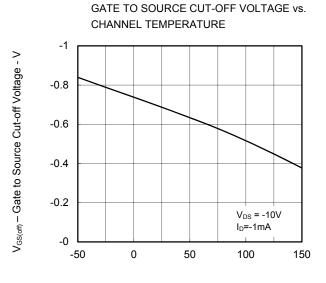




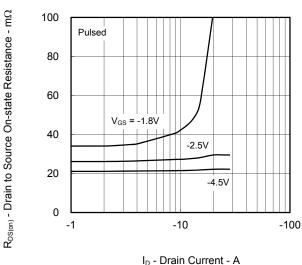
T_A -Ambient Temperature - °C





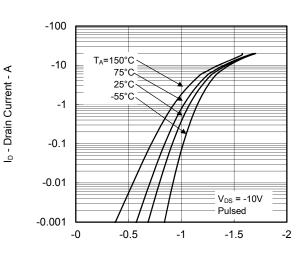


T_{ch} - Channel Temperature - °C



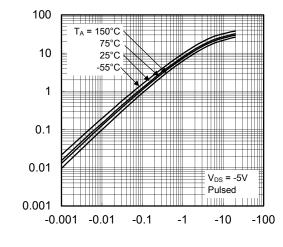
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

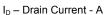
FORWARD TRANSFER CHARACTERISTICS

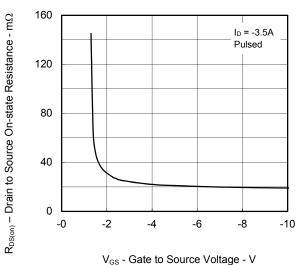


V_{GS} - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



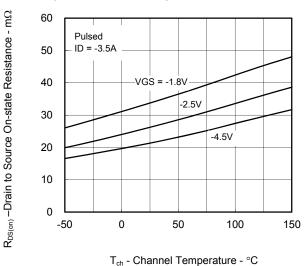




DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

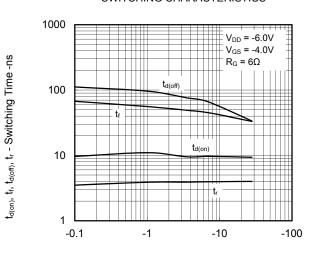
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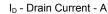
| y_{fs} | - Forward Transfer Admittance - S

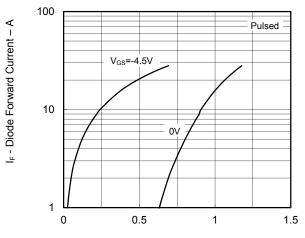


DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



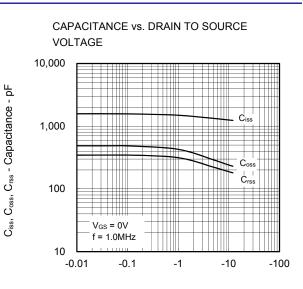






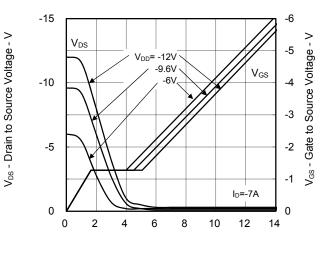
SOURCE TO DRAIN DIODE FORWARD VOLTAGE

 $V_{F(S\!-\!D)}$ - Drain to Source Voltage - V



V_{DS} – Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

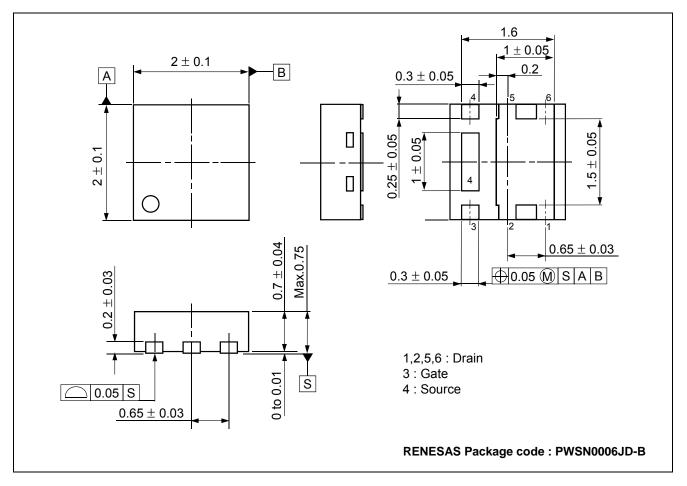


Q_G - Gate Charge - nC

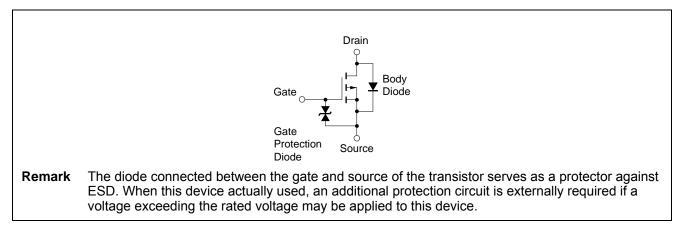


Package Drawings (Unit: mm)

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Equivalent Circuit





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